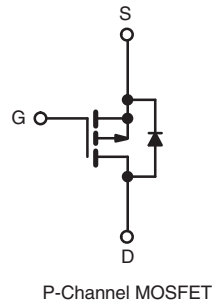
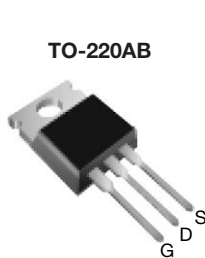


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 100	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	0.30
Q_g (Max.) (nC)	38	
Q_{gs} (nC)	6.8	
Q_{gd} (nC)	21	
Configuration	Single	



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available

RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF9530PbF
	SiHF9530-E3
SnPb	IRF9530
	SiHF9530


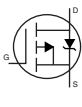
ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	- 100	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25$ °C	I_D	- 12	A
		$T_C = 100$ °C		- 8.2	
Pulsed Drain Current ^a			I_{DM}	- 48	
Linear Derating Factor				0.59	W/°C
Single Pulse Avalanche Energy ^b			E_{AS}	400	mJ
Repetitive Avalanche Current ^a			I_{AR}	- 12	A
Repetitive Avalanche Energy ^a			E_{AR}	8.8	mJ
Maximum Power Dissipation	$T_C = 25$ °C		P_D	88	W
Peak Diode Recovery dV/dt^c			dV/dt	- 5.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)		for 10 s		300 ^d	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = - 25$ V, starting $T_J = 25$ °C, $L = 4.2$ mH, $R_g = 25$ Ω , $I_{AS} = - 12$ A (see fig. 12).
- $I_{SD} \leq - 12$ A, $dI/dt \leq 140$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.

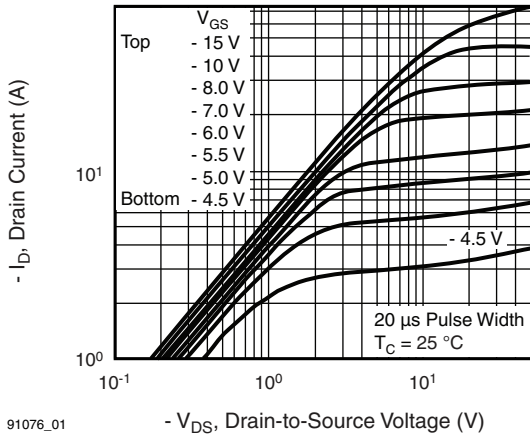
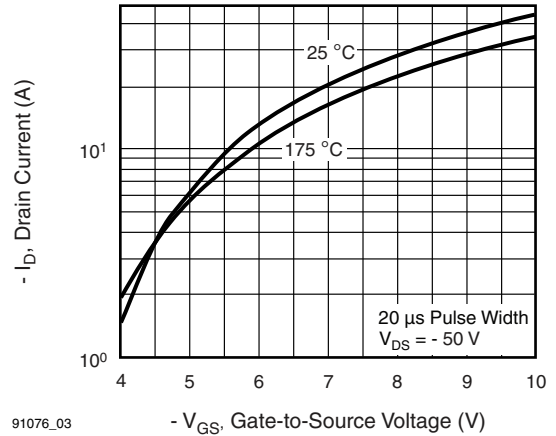
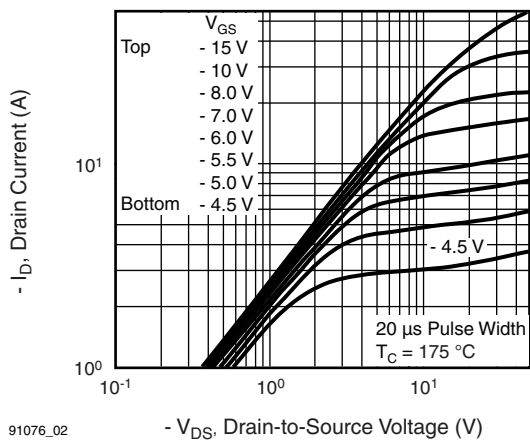
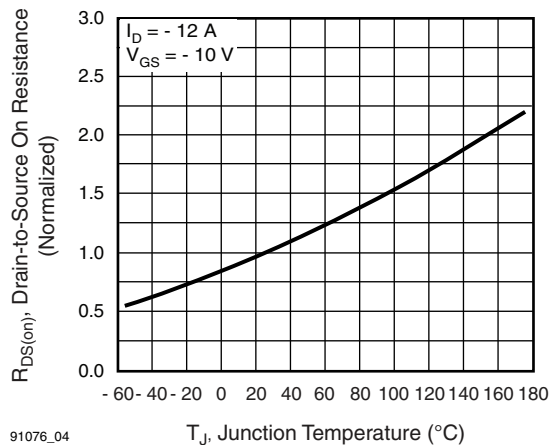
* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.10	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -7.2\text{ A}^b$	-	-	0.30	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -7.2\text{ A}^b$	3.7	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	860	-	pF
Output Capacitance	C_{oss}		-	340	-	
Reverse Transfer Capacitance	C_{rss}		-	93	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}, I_D = -12\text{ A}, V_{DS} = -80\text{ V}$, see fig. 6 and 13 ^b	-	-	38	nC
Gate-Source Charge	Q_{gs}		-	-	6.8	
Gate-Drain Charge	Q_{gd}		-	-	21	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -12\text{ A}, R_g = 12\text{ }\Omega, R_D = 3.9\text{ }\Omega$, see fig. 10 ^b	-	12	-	ns
Rise Time	t_r		-	52	-	
Turn-Off Delay Time	$t_{d(off)}$		-	31	-	
Fall Time	t_f		-	39	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode	-	-	-12	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-48	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -12\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	-6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -12\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	120	240	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.46	0.92	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25 \text{ }^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 175 \text{ }^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature

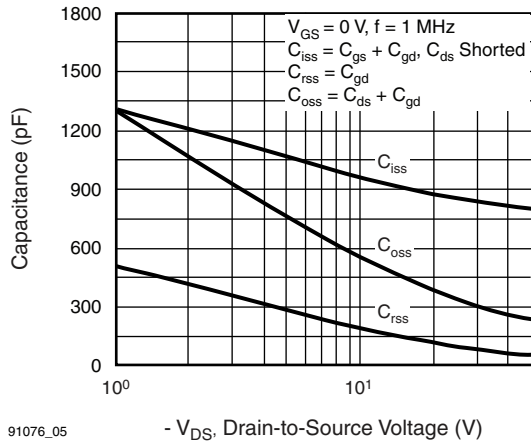


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

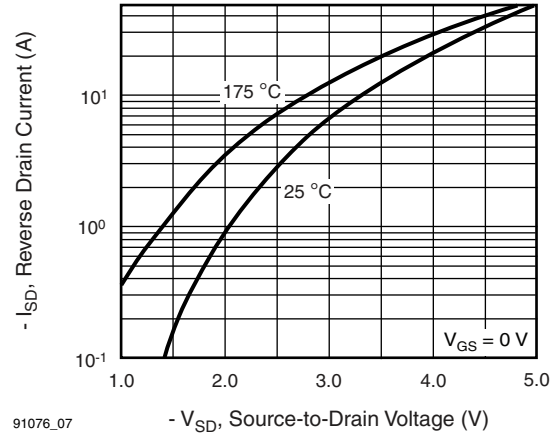


Fig. 7 - Typical Source-Drain Diode Forward Voltage

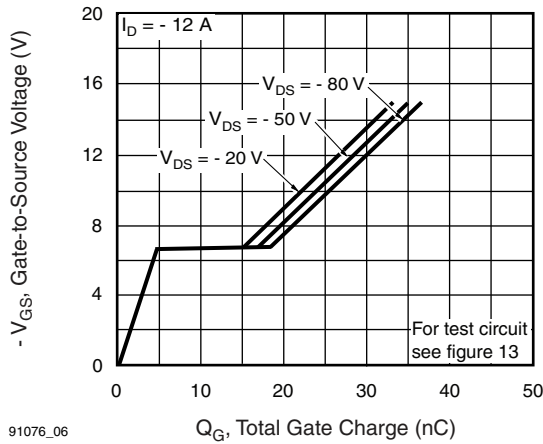


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

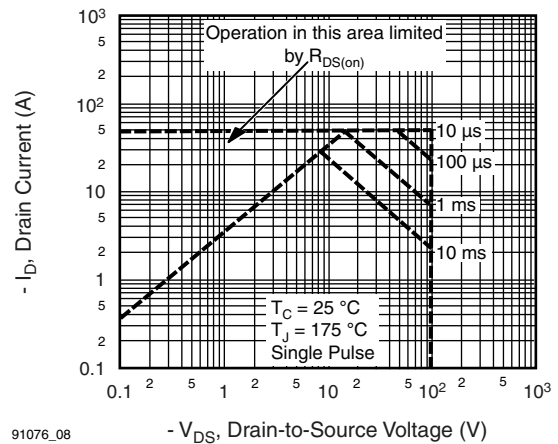


Fig. 8 - Maximum Safe Operating Area

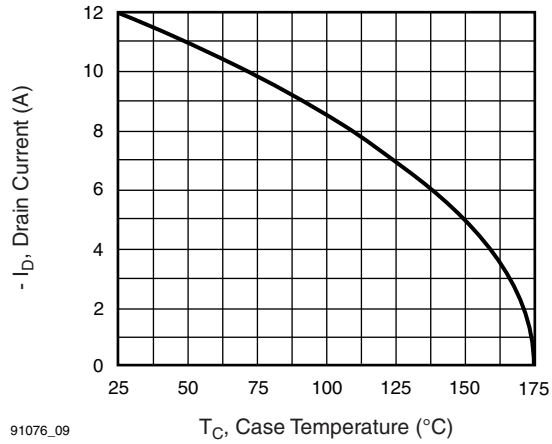


Fig. 9 - Maximum Drain Current vs. Case Temperature

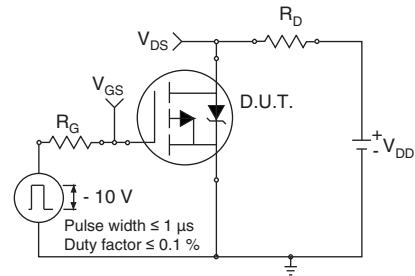


Fig. 10a - Switching Time Test Circuit

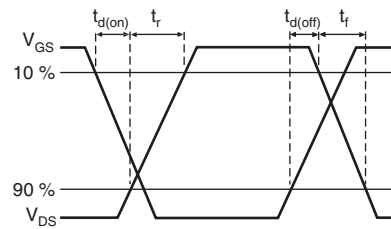


Fig. 10b - Switching Time Waveforms

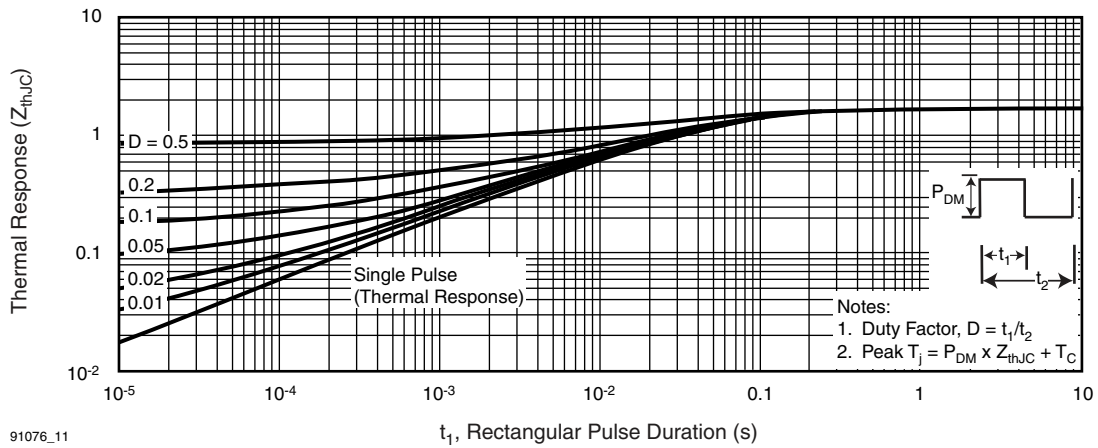


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

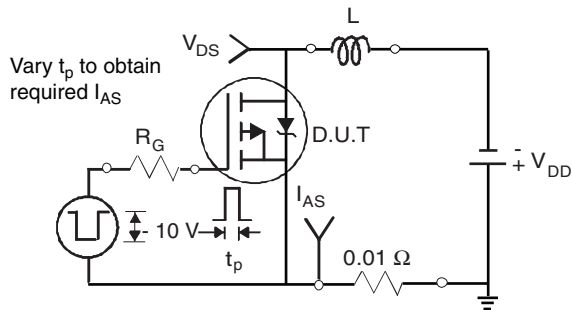


Fig. 12a - Unclamped Inductive Test Circuit

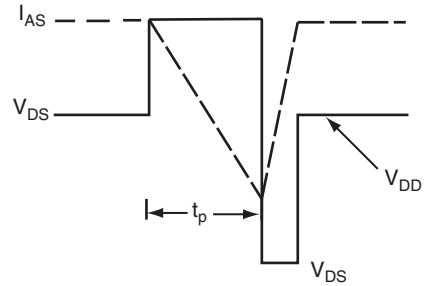


Fig. 12b - Unclamped Inductive Waveforms

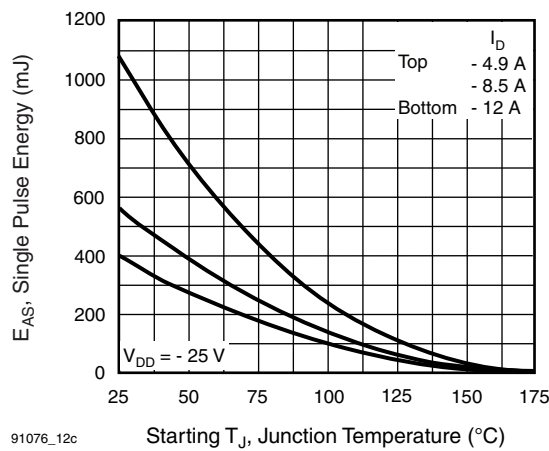


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

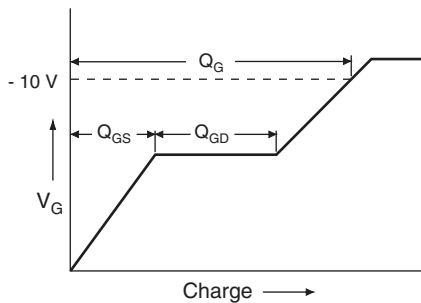


Fig. 13a - Basic Gate Charge Waveform

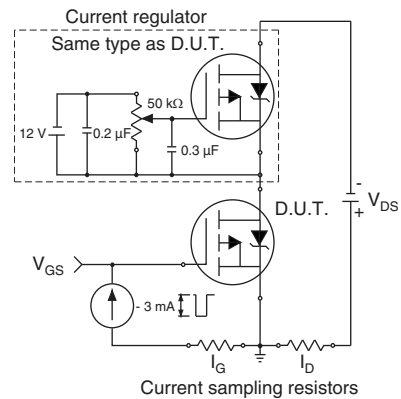
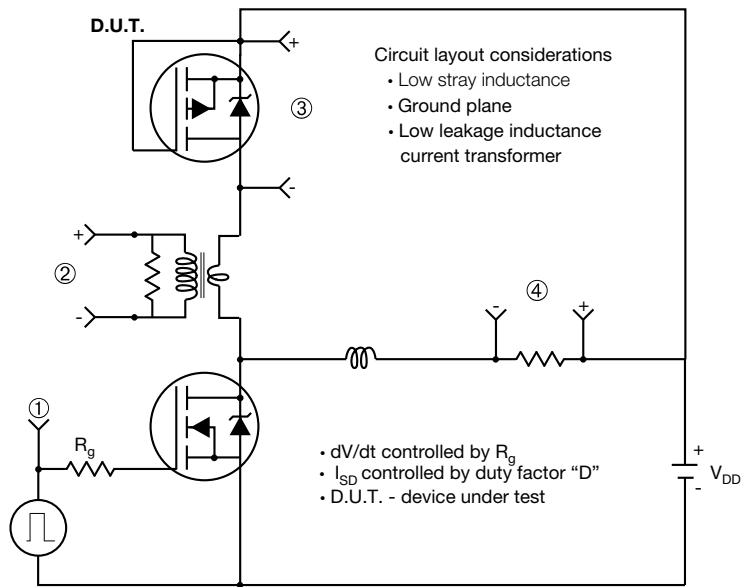
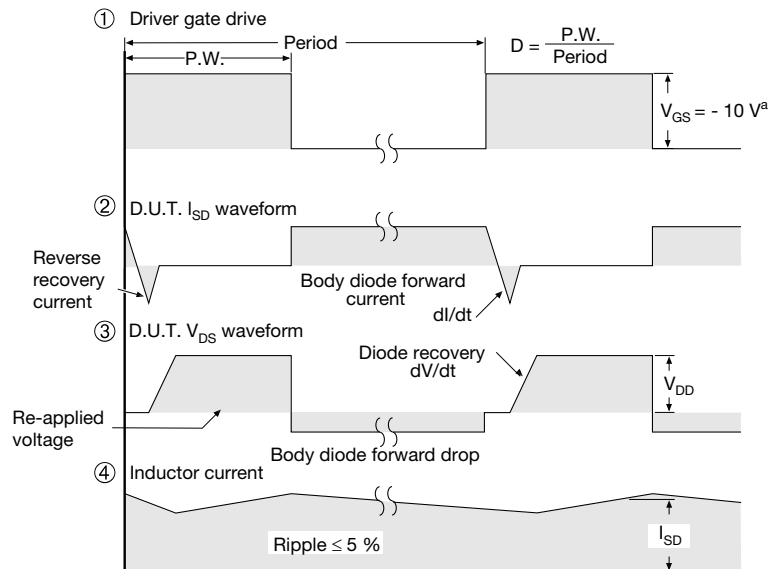


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit


Note
 • Compliment N-Channel of D.U.T. for driver



Note
 a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91076.

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

- * M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM
- Xi'an and Mingxin actual photo





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<http://moschip.ru/get-element>

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